

## **Features and Benefits**

- Each half-bridge circuit consists of a pre-driver circuit that is completely independent from the others
- 10 to 30 A continuous output IPM in a small-footprint package
- · Protection against simultaneous high- and low-side turning on
- Bootstrap diodes with series resistors for suppressing inrush current are incorporated
- CMOS compatible input (3.3 to 5 V)
- Designed to minimize simultaneous current through both high- and low-side IGBTs by optimizing gate drive resistors
- Integrated Fast Recovery Diode (FRD) as freewheeling diode for each IGBT
- UVLO protection with auto restart
- Thermal shutdown (TSD) with auto restart
- Fault (FO indicator) signal output at protection activation: UVLO (low side only), OCP, STP, and TSD
- Proprietary power DIP package
- UL Recognized Component (File No.: E118037)

## Packages: Power DIP



## Description

The SCM1240M inverter power module (IPM) devices provide a robust, highly-integrated solution for optimally controlling 3-phase motor power inverter systems and variable speed control systems used in energy-conserving designs to drive motors of residential and commercial appliances. These ICs take 85 to 253 VAC input voltage, and 10 to 30 A (continuous) output current. They can withstand voltages of up to 600 V (IGBT breakdown voltage).

The high current SCM1240M employs a new, small-footprint proprietary DIP package. The IC itself consists of all of the necessary power elements (six IGBTs), pre-drive ICs (three), and freewheeling diodes (six), needed to configure the main circuit of an inverter, as well as a bootstrap circuit (three bootstrap diodes and three boot resistors) as a high-side drive power supply. This enables the main circuit of the inverter to be configured with fewer external components than traditional designs.

Applications include residential white goods (home appliances) and commercial appliance motor control, such as:

- Air conditioner compressor motor
- Air conditioner fan motor
- Refrigerator compressor motor
- Washing machine main motor

## **Functional Block Diagram**



Figure 1. Diagram of one of three phases in the device.

### **Selection Guide**

			IGBT Breakdown	IGBT Saturation	Output	Current
Part Number	Package	Packing Voltage, V <sub>CES</sub> (min) (V)		Voltage, V <sub>CE(sat)</sub> (typ) (V)	Continuous, I <sub>o</sub> (max) (A)	Pulsed, I <sub>OP</sub> (max) (A)
SCM1241M	Fully Molded	10 pieces per tube	600	1.7	10	20
SCM1243MF	Heatsink Pad	10 pieces per tube	600	1.7	15	30
SCM1245MF	Heatsink Pad	10 pieces per tube	600	1.7	20	30
SCM1246MF	Heatsink Pad	10 pieces per tube	600	1.7	30	45

## Absolute Maximum Ratings, valid at $T_A = 25^{\circ}C$

Characteristic	Symbol		Remarks		Units
Supply Voltage	V <sub>DC</sub>	Between VBB a	tween VBB and LS1, LS2, and LS3		
Supply Voltage (Surge)	V <sub>DC(surge)</sub>	Between VBB a	etween VBB and LS1, LS2, and LS3		V
IGBT Breakdown Voltage	V <sub>CES</sub>	$V_{\rm CC}$ = 15 V, I <sub>C</sub> =	1 mA, V <sub>IN</sub> = 0 V	600	V
Logic Supply Voltage	V <sub>CC</sub>	Between VCC a	and COM	20	V
Boot-strap Voltage	V <sub>BS</sub>	Between VB an	d HS (U,V,W)	20	V
		SCM1241M	T <sub>Case</sub> = 25°C	10	Adc
Outrut Current, Continuous		SCM1243MF	T <sub>Case</sub> = 25°C	15	Adc
Output Current, Continuous	lo	SCM1245MF	T <sub>Case</sub> = 25°C	20	Adc
		SCM1246MF	T <sub>Case</sub> = 25°C	30	Adc
		SCM1241M	Pulse Width ≤1 ms	20	Α
Outrast Outrast Dutast	I <sub>OP</sub>	SCM1243MF	Pulse Width ≤1 ms	30	Α
Output Current, Pulsed		SCM1245MF	Pulse Width ≤1 ms	30	Α
		SCM1246MF	Pulse Width ≤1 ms	45	Α
Input Voltage	V <sub>IN</sub>	HIN, LIN, and C	HIN, LIN, and OCP		V
FO Terminal Voltage	V <sub>FO</sub>	Between FO ar	Between FO and COM		V
		SCM1241M		6.0	°C/W
Thermal Desistance, Junction to Occo	R <sub>(j-c)Q</sub>	SCM1243MF SCM1245MF SCM1246MF	1 element operation (IGBT)	3.0	°C/W
Thermal Resistance, Junction-to-Case		SCM1241M		6.5	°C/W
	R <sub>(j-c)F</sub>	SCM1243MF SCM1245MF SCM1246M	1 element operation (FRD)	4.0	°C/W
Case Operating Temperature	T <sub>OPC</sub>			-20 to 100	°C
Junction Temperature (IGBT)	TJ			150	°C
Storage Temperature	T <sub>stg</sub>			-40 to 150	°C
Isolation Voltage	V <sub>iso</sub>	Between expos	ed thermal pad and each pin; 1 minute, ac	2000	V <sub>rms</sub>

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature,  $T_A$ , of 25°C, unless otherwise stated.

### **Recommended Operating Conditions**

Characteristic	Symbol		Remarks	Min.	Тур.	Max.	Units
Main Supply Voltage	V <sub>DC</sub>	Between VBB	-	300	400	V	
Logic Supply Voltage	V <sub>CC</sub>	Between VCC	and COM	13.5	-	16.5	V
Logic Supply Voltage	V <sub>BS</sub>	Between VB a	nd HS	13.5	-	16.5	V
Minimum Innut Dulan Width	t <sub>INmin(on)</sub>	On pulse		0.5	-	-	μs
Minimum Input Pulse Width	t <sub>INmin(off)</sub>	Off pulse		0.5	-	-	μs
Dead Time*	t <sub>dead</sub>			1.0	-	-	μs
FO Pull-up Resistor	R <sub>FO</sub>			1	-	22	kΩ
FO Pull-up Voltage	V <sub>FO</sub>			3.0	-	5.5	V
Bootstrap Capacitor	C <sub>BOOT</sub>			10	-	220	μF
		SCM1241M	For I <sub>P</sub> ≤ 20 A	27	_	-	mΩ
Shunt Resistor	Rs	SCM1243MF SCM1245MF SCM1246MF	For I <sub>P</sub> ≤ 30 A	15	_	_	mΩ
RC Filter Resistor	Ro			-	-	100	Ω
RC Filter Capacitor	Co			-	-	2200	pF
PWM Carrier Frequency	f <sub>C</sub>			-	_	20	kHz
Junction Temperature	TJ			-	-	125	°C

\*Dead Time must be controlled from an external source.



Typical Application Diagram

Typical application utilizing one shunt resistor, RS

See application notes on next page.

### Notes for Typical Application Diagram

- To use the OCP circuit shown in the Typical Application drawing, an external shunt resistor, RS, is needed. The RS value depends on how many low-side IGBTs turn on simultaneously.
- To avoid malfunction, the wiring between the LS and COM pins should be as short as possible.
- To prevent surge destruction, put a 0.01 to 1 µF snubber capacitor, CS, in parallel with the electrolytic capacitor.
- To prevent surge destruction, put a 18 to 20 V Zener diode between the VCC and COM pins.
- To prevent surge malfunction, put a 0.01 to 0.1 µF ceramic capacitor between the VCC and COM pins and the VB and HS pins.
- To add an external low pass filter, place RO and CO between the A to D pin of the application controller and shunt resistor RS, ensuring that the time constant of this low pass filter is less than 0.2 µs. The internal OCP circuit has a 1.5 µs (min) filtering delay.

However, the low pass filter causes an additional delay to detecting an overcurrent condition of the SCM1240M, and if the total delay exceeds 1.7  $\mu$ s, permanent damage to the SCM1240M may result.

- To suppress noise, connect a resistor, RF, and capacitor, CF, to the  $\overline{FOx}$  pins. Also, when an overcurrent condition is detected, the  $\overline{FOx}$  pin goes low for 25 µs (typ) as an active low fault flag, and then returns up to its normal state. It is recommended to connect the  $\overline{FOx}$  pin directly to an interrupt pin of the external controller, to ensure the 25 µs interval is detected.
- To provide the best thermal shutdown protection (TSD), it is strongly recommended that the three FOx pins be tied together. In this way an overtemperature event (internal temperature rise above 150°C) in any of the three phases will cause all three phases to shut down. If the FOx pins are not tied together, but are independently pulled up to +5 V, the TSD function for each phase shuts down only that phase.

### ELECTRICAL CHARACTERISTICS, valid at T<sub>A</sub>=25°C, unless otherwise noted

Characteristics	Symbol	Conditions	Min	Тур	Max	Units
Logic Supply Voltage	V <sub>CC</sub>	Between VCC and COM	13.5	-	16.5	V
Logic Supply Current	Icc	V <sub>CC</sub> = 15 V, 3 phases operating	_	3	-	mA
Bootstrap Supply Current	I <sub>BS</sub>	VB – HS = 15 V, one phase operating	_	140	_	μA
	VIH	V <sub>CC</sub> = 15 V, output on	-	2.0	2.5	V
Input Voltage	V <sub>IL</sub>	V <sub>CC</sub> = 15 V, output off	1.0	1.5	-	V
Input Voltage Hysteresis	V <sub>lhys</sub>	V <sub>CC</sub> = 15 V	-	0.5	-	V
han at Querrant	I <sub>IHH</sub>	V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 5 V	_	230	500	μA
Input Current	I <sub>ILH</sub>	V <sub>CC</sub> = 15 V, V <sub>IN</sub> = 0 V	_	_	2	μA
	U <sub>VHL</sub>	N/ 45.1/	10.0	11.0	12.0	V
Undervoltage Lock Out (High Side)	U <sub>VHH</sub>	V <sub>CC</sub> = 15 V	10.5	11.5	12.5	V
	U <sub>VLL</sub>	N/ 45.1	10.0	11.0	12.0	V
Undervoltage Lock Out (Low Side)	U <sub>VLH</sub>	$V_{\rm CC} = 15 V$	10.5	11.5	12.5	V
	V <sub>FOL</sub>		_	_	0.5	V
FO Terminal Output Voltage	V <sub>FOH</sub>	$V_{CC}$ = 15 V, $V_{FO}$ = 5 V, $R_{FO}$ = 10 k $\Omega$	4.8	_	_	V
Overcurrent Protection Trip Voltage	V <sub>TRIP</sub>	V <sub>CC</sub> = 15 V	0.46	0.50	0.54	V
Overcurrent Protection Hold Time	t <sub>P</sub>	V <sub>CC</sub> = 15 V	20	25	_	μs
Overtemperature Protection Activation	T <sub>DH</sub>			150	165	°C
and Releasing Temperature	T <sub>DL</sub>	V <sub>CC</sub> = 15 V	105	120	135	°C
Blanking Time	t <sub>blank</sub>	V <sub>CC</sub> = 15 V	_	1.65	_	μs
IGBT Breakdown Voltage	V <sub>CES</sub>	V <sub>CC</sub> = 15 V, I <sub>C</sub> = 1 mA, V <sub>IN</sub> = 0 V	600	_	_	V
IGBT Leakage Current	I <sub>CES</sub>	V <sub>CC</sub> = 15 V, V <sub>CE</sub> = 600 V, V <sub>IN</sub> = 0 V	_	_	1	mA
		SCM1241M V <sub>CC</sub> = 15 V, I <sub>C</sub> = 10 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
		SCM1243MF V <sub>CC</sub> = 15 V, I <sub>C</sub> = 15 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
IGBT Saturation Voltage	V <sub>CE(sat)</sub>	SCM1245MF V <sub>CC</sub> = 15 V, I <sub>C</sub> = 20 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
		SCM1246MF V <sub>CC</sub> = 15 V, I <sub>C</sub> = 30 A, V <sub>IN</sub> = 5 V	_	1.7	2.2	V
		SCM1241M V <sub>CC</sub> = 15 V, I <sub>F</sub> = 10 A, V <sub>IN</sub> = 0 V	_	1.9	2.4	V
		SCM1243MF V <sub>CC</sub> = 15 V, I <sub>F</sub> = 15 A, V <sub>IN</sub> = 0 V	_	1.75	2.2	V
Diode Forward Voltage	V <sub>F</sub>	SCM1245MF V <sub>CC</sub> = 15 V, I <sub>F</sub> = 20 A, V <sub>IN</sub> = 0 V	_	1.9	2.4	V
		SCM1246MF V <sub>CC</sub> = 15 V, I <sub>F</sub> = 30 A, V <sub>IN</sub> = 0 V	_	1.5	2.0	V
Diode Recovery Time (Bootstrap)	t <sub>rr</sub>	$I_{F} = I_{RECOVERY(PEAK)} = 100 \text{ mA}$		70	_	ns
Diode Leakage Current (Boot Strap)	I <sub>IB</sub>	V <sub>R</sub> = 600 V	_	_	10	μA
Diode Forward Voltage (Boot Strap)	V <sub>FB</sub>	I <sub>F</sub> = 0.15 A	_	1.1	1.3	V
Diode Series Resistor (Boot Strap)	R <sub>B</sub>		17.6	22.0	26.4	Ω

Continued on the next page...

### ELECTRICAL CHARACTERISTICS, valid at T<sub>A</sub>=25°C, unless otherwise noted

Characteristics	Symbol		Conditions	Min	Тур	Max	Units
	t <sub>dH(on)</sub>			-	590	-	ns
	t <sub>rH</sub>			-	80	-	ns
	t <sub>rrH</sub>	SCM1241M	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 10 A, inductive load: HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	-	60	-	ns
	t <sub>dH(off)</sub>			-	550	_	ns
	t <sub>fH</sub>			-	90	_	ns
	t <sub>dH(on)</sub>			-	600	-	ns
	t <sub>rH</sub>			-	70	-	ns
	t <sub>rrH</sub>	SCM1243MF	V <sub>DC</sub> = 300 V, V <sub>CC</sub> = 15 V, I <sub>C</sub> = 15 A, inductive load; HIN = $0 \rightarrow 5$ V or $5 \rightarrow 0$ V	-	70	-	ns
	t <sub>dH(off)</sub>			-	620	-	ns
High Side Switching Time	t <sub>fH</sub>			-	60	_	ns
High Side Switching Time	t <sub>dH(on)</sub>	SCM1245MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_{C}$ = 20 A, inductive load; HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	-	695	_	ns
	t <sub>rH</sub>			-	95	_	ns
	t <sub>rrH</sub>			-	75	_	ns
	t <sub>dH(off)</sub>			-	675	-	ns
	t <sub>fH</sub>			-	55	-	ns
	t <sub>dH(on)</sub>			-	660	_	ns
	t <sub>rH</sub>			_	110	_	ns
	t <sub>rrH</sub>	SCM1246MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 30 A, inductive load; HIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	_	60	_	ns
	t <sub>dH(off)</sub>			_	700	_	ns
	t <sub>fH</sub>			_	50	_	ns

Continued on the next page...

### ELECTRICAL CHARACTERISTICS, valid at $T_A=25^{\circ}C$ , unless otherwise noted

Characteristics	Symbol		Conditions	Min	Тур	Max	Units
	t <sub>dL(on)</sub>			_	570	-	ns
	t <sub>rL</sub>			_	100	_	ns
	t <sub>rrL</sub>	SCM1241M	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 10 A, inductive load: LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	-	70	-	ns
	t <sub>dL(off)</sub>			-	560	-	ns
	t <sub>fL</sub>			-	100	_	ns
	t <sub>dL(on)</sub>			-	600	-	ns
	t <sub>rL</sub>			-	100	_	ns
	t <sub>rrL</sub>	SCM1243MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 15 A, inductive load; LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	-	80	_	ns
	t <sub>dL(off)</sub>			-	600	-	ns
Low Cide Custoking Time	t <sub>fL</sub>			-	70	-	ns
Low Side Switching Time	t <sub>dL(on)</sub>	SCM1245MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 20 A, inductive load; LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	-	715	-	ns
	t <sub>rL</sub>			-	135	_	ns
	t <sub>rrL</sub>			-	115	_	ns
	t <sub>dL(off)</sub>			-	670	_	ns
	t <sub>fL</sub>			-	50	_	ns
	t <sub>dL(on)</sub>			-	660	_	ns
	t <sub>rL</sub>			_	150	_	ns
	t <sub>rrL</sub>	SCM1246MF	$V_{DC}$ = 300 V, $V_{CC}$ = 15 V, $I_C$ = 30 A, inductive load: LIN = 0 $\rightarrow$ 5 V or 5 $\rightarrow$ 0 V	-	70	_	ns
	t <sub>dL(off)</sub>			_	690	_	ns
	t <sub>fL</sub>				50	_	ns



Switching Timing Definitions

Mode	HINx	LINx	High-side MOSFET	Low-side MOSFET
	L	L	Off	Off
N	Н	L	On	Off
Normal <sup>1</sup>	L	н	Off	On
	Н	н	Off	Off
	L	L	Off	Off
TOD	Н	L	Off	Off
TSD	L	н	Off	Off
	Н	н	Off	Off
	L	L	Off	Off
000	Н	L	Off	Off
OCP	L	н	Off	Off
	Н	н	Off	Off
	L	L	Off	Off
	Н	L	Off	Off
VCCx UVLO <sup>2</sup>	L	н	Off	Off
	Н	н	Off	Off
	L	L	Off	Off
	Н	L	Off	Off
VBx UVLO <sup>3</sup>	L	н	Off	On
	Н	н	Off	Off
	L	L	Off	Off
FOx Low	Н	L	Off	Off
FUXLOW	L	н	Off	Off
	Н	Н	Off	Off

### Input-Output Truth Table

<sup>1</sup>In the case where a pair of HINx and LINx signals are asserted at the same time, the shoot-through prevention feature sets both the high-side and the low-side IGBTs off.

<sup>2</sup>After the VCCx power rail recovers from a UVLO condition, a rising edge of HINx starts driving the highside IGBT (edge trigger). On the other hand, after the UVLO condition is released, the input level of the LINx pins reflects the state of the low-side IGBTs (level trigger).

<sup>3</sup>After the VBx power rail recovers from a UVLO condition, a rising edge of HINx starts driving the highside IGBT (edge trigger).

## **Pin-out Diagram** 凡 凡



(Bottom View)

## **Terminal List Table**

Name	Number	Function
1	FO1	U phase fault output for overcurrent and UVLO detected
2	OCP1	Input for U phase overcurrent protection
3	LIN1	Signal input for low-side U phase (active high)
4	COM1	Supply ground for U phase IC
5	HIN1	Signal input for high-side U phase (active high)
6	VCC1	Supply voltage for U phase IC
7	VB1	High-side floating supply voltage for U phase
8	HS1	High-side floating supply ground for U phase
9	FO2	V phase fault output for overcurrent and UVLO detected
10	OCP2	Input for V phase overcurrent protection
11	LIN2	Signal input for low-side V phase (active high)
12	COM2	Supply ground for V phase IC
13	HIN2	Signal input for high-side V phase (active high)
14	VCC2	Supply voltage for V phase IC
15	VB2	High-side floating supply voltage for V phase
16	HS2	High-side floating supply ground for V phase
17	FO3	W phase fault output for overcurrent and UVLO detected
18	OCP3	Input for W phase overcurrent protection
19	LIN3	Signal input for low-side W phase (active high)
20	COM3	Supply ground for W phase IC
21	HIN3	Signal input for high-side W phase (active high)
22	VCC3	Supply voltage for W phase IC
23	VB3	High-side floating supply voltage for W phase
24	HS3	High-side floating supply ground for W phase
25	VBB	Positive DC bus supply voltage
26	W	Output for W phase
27	LS3	Negative DC bus supply ground for W phase
28	VBB	(Pin trimmed) positive DC bus supply voltage
29	V	Output for V phase
30	LS2	Negative DC bus supply ground for V phase
31	VBB	(Pin trimmed) positive DC bus supply voltage
32	U	Output for U phase
33	LS1	Negative DC bus supply ground for U phase

## SCM1240M

High-Side Driver Input/Output and UVLO Protection

## High Voltage, High Current 3-Phase Motor Drivers

Low-Side Driver Input/Output and UVLO Protection

#### $V_{CC}$ = 15 V VB – HS = 15 V HIN ни LIN LIN UVHH UVLH UVHL UVLL VB-HS vcc но но LO FO \*No FO output at H-side UVLO FO \*HO starts from positive edge after UVLO release \*LO starts after UVLO release **Shoot-Through Prevention Thermal Shutdown** $V_{CC}$ , VB - HS = 15 VHIN HIN-LIN LIN TDH Tmic VCC VB HO но LO FO FO \*Tmic is the temperature of the predriver IC (MIC) \* While both HIN and LIN are in high state HO and LO turn off and FO signals out. \*HO and LO start after TSD release

### Timing Diagrams

(one phase of three phases)

**Overcurrent Protection** 



### PACKAGE OUTLINE DRAWING



Device composition complies with the RoHS directive.

SANKEN ELECTRIC CO., LTD.



Device composition complies with the RoHS directive.

SANKEN ELECTRIC CO., LTD.



Device composition complies with the RoHS directive.

SANKEN ELECTRIC CO., LTD.

## **MECHANICAL CHARACTERISTICS**

Characteristic	Remarks	Min.	Тур.	Max.	Units
Heataink Mounting Scrow Torque	Use one M3 screw each end	58.8	-	78.4	N•cm
Heatsink Mounting Screw Torque		6.0	Ι	8.0	kgf•cm
Flatness of Heatsink Attachment Area	Refer to figure below	0	-	200	μm
Deckage Waight	SCM1241M	-	10.8	_	g
Package Weight	SCM124xMF	-	11.8	-	g





## SCM1240M

## High Voltage, High Current 3-Phase Motor Drivers





WARNING — These devices are designed to be operated at lethal voltages and energy levels. Circuit designs that embody these components must conform with applicable safety requirements. Precautions must be taken to prevent accidental contact with power-line potentials. Do not connect grounded test equipment.

The use of an isolation transformer is recommended during circuit development and breadboarding.

Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

#### **Cautions for Storage**

- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40 to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of product that has been stored for a long time.

### **Cautions for Testing and Handling**

- When tests are carried out during inspection testing and other standard test periods, protect the product from power surges from the testing device, shorts between adjacent product packages, and shorts to the heatsink.
- The screwing torque for attaching a heatsink shall be 58.8 to 78.4 N•cm (6.0 to 8.0 Kgf•cm).
- Ensure there are no foreign objects between the heatsink and thermal pad; only silicone thermal grease is allowed.

### **Remarks About Using Silicone Grease with a Heatsink**

- When silicone grease is used in mounting this product with a heatsink, grease shall be applied evenly and thinly. If more silicone grease than required is applied, it may produce stress.
- Volatile-type silicone greases may permeate the product and produce cracks after long periods of time, resulting in reduced heat radiation effect, and possibly shortening the lifetime of the product.
- Hard silicone greases may cause cracks in the product when screwing the product to a heatsink.

 Our recommended silicone greases for heat radiation purposes, which will not cause any adverse effect on the product life, are indicated below:

 Туре	Suppliers
 G746	Shin-Etsu Chemical Co., Ltd.
YG6260	Momentive Performance Materials Holding, Inc.
SC102	Dow Corning Toray Silicone Co., Ltd.

#### Soldering

 When soldering the product, please be sure to minimize the working time, within the following limits: 260±5°C 10 s

380±5°C 5 s

 Soldering iron should be at a distance of at least 1.5 mm from the body of the product

### Electrostatic Discharge

- When handling the product, operator must be grounded. Grounded wrist straps worn should have at least 1 MΩ of resistance to ground to prevent shock hazard.
- Workbenches where the product is handled should be grounded and be provided with conductive table and floor mats.
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the product, the head of soldering irons or the solder bath must be grounded in other to prevent leak voltages generated by them from being applied to the product.
- The product should always be stored and transported in our shipping containers or conductive containers, or be wrapped in aluminum foil.

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- In the case that you use our semiconductor devices or design your products by using our semiconductor devices, the reliability largely depends on the degree of derating to be made to the rated values. Derating may be interpreted as a case that an operation range is set by derating the load from each rated value or surge voltage or noise is considered for derating in order to assure or improve the reliability. In general, derating factors include electric stresses such as electric voltage, electric current, electric power etc., environmental stresses such as ambient temperature, humidity etc. and thermal stress caused due to self-heating of semiconductor devices. For these stresses, instantaneous values, maximum values and minimum values must be taken into consideration.
  In addition, it should be noted that since power devices or IC's including power devices have large self-heating value, the degree of derating of junction temperature (T<sub>1</sub>) affects the reliability significantly.
- When using the products specified herein by either (i) combining other products or materials therewith or (ii) physically, chemically or otherwise processing or treating the products, please duly consider all possible risks that may result from all such uses in advance and proceed therewith at your own responsibility.
- · Anti radioactive ray design is not considered for the products listed herein.
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